

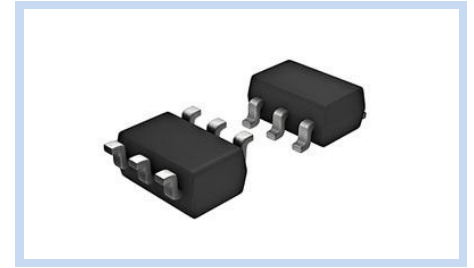
Transistor Dual PNP 65V 0.2W SOT-363

BC856BS

MERITEK

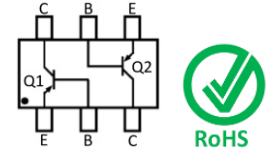
FEATURE

- Low Current, Low Voltage
- No Mutual Interference between The Transistors
- Application: Switching and Amplifier



MECHANICAL DATA

- Case: SOT-363, Molded Epoxy Meets UL94V-0
- Terminals: Solderable per MIL-STD-202, Method 208



MAXIMUM RATING

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-65	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-100	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	-55 ~+150	°C

ELECTRICAL CHARACTERISTICS

Parameter- ON Characteristic	Conditions	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain	$V_{CE} = -5V, I_C = -2mA$	h_{FE}	220	-	475	-
Collector-Emitter Saturation Voltage	$I_C = -10mA, I_B = -0.5mA$	$V_{CE(SAT)}$	-	-	-0.30	V
	$I_C = -100mA, I_B = -5mA$		-	-	-0.65	
Base-Emitter on Voltage	$V_{CE} = -5V, I_C = -2mA$	$V_{BE(ON)}$	-0.60	-	-0.75	V
	$V_{CE} = -5V, I_C = -10mA$		-	-	-0.82	
Parameter- OFF Characteristics	Conditions	Symbol	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$I_C = -10\mu A, I_E = 0$	$V_{(BR)CBO}$	-80	-	-	V
Collector-Emitter Breakdown Voltage	$I_C = -10mA, I_B = 0$	$V_{(BR)CEO}$	-65	-	-	V
Emitter-Base Breakdown Voltage	$I_E = -10\mu A, I_C = 0$	$V_{(BR)EBO}$	-5	-	-	V
Collector Base Cut-Off Current	$V_{CB} = -30V, I_E = 0$	I_{CBO}	-	-	-15	nA
Emitter Base Cut-Off Current	$V_{EB} = -5V, I_C = 0$	I_{EBO}	-	-	-100	nA
Output Capacitance	$V_{CB} = -10V, f = 1MHz$	C_{ob}	-	-	4.5	pF
Parameter-Small Signal	Conditions	Symbol	Min.	Typ.	Max.	Unit
Current-Gain – Bandwidth Product	$V_{CE} = -5V, I_C = -10mA, f = 100MHz$	f_T	100	-	-	MHz

Note:

1. $T_A = 25^\circ C$ unless otherwise noted

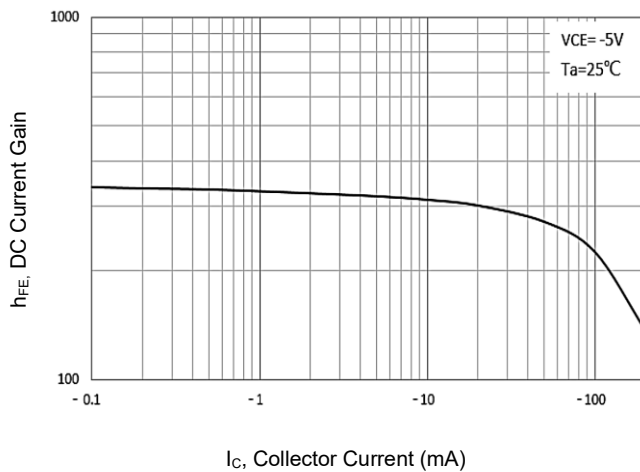
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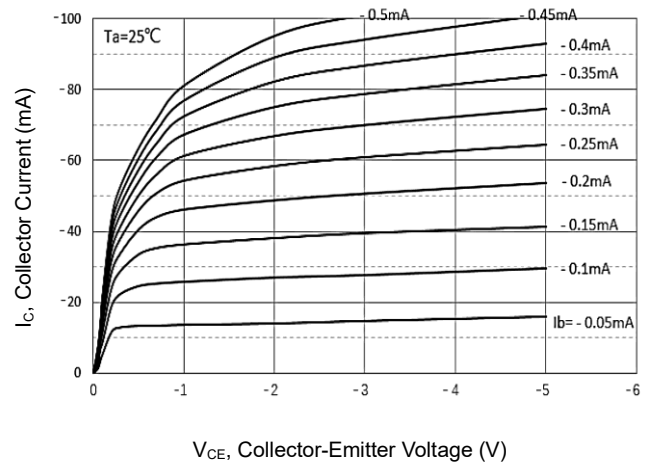
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CHARACTERISTIC CURVES

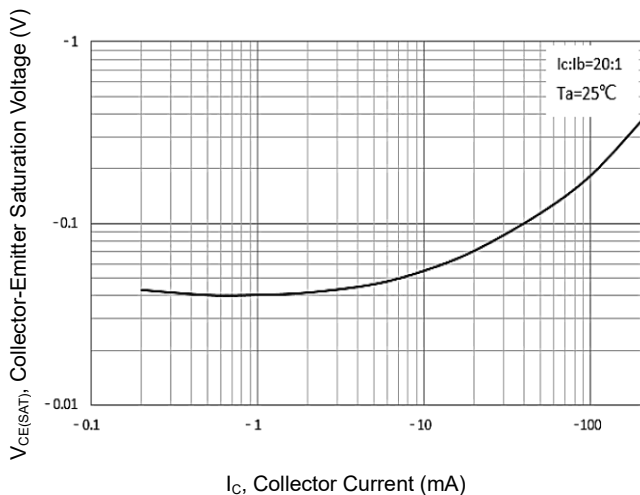
DC Current Gain



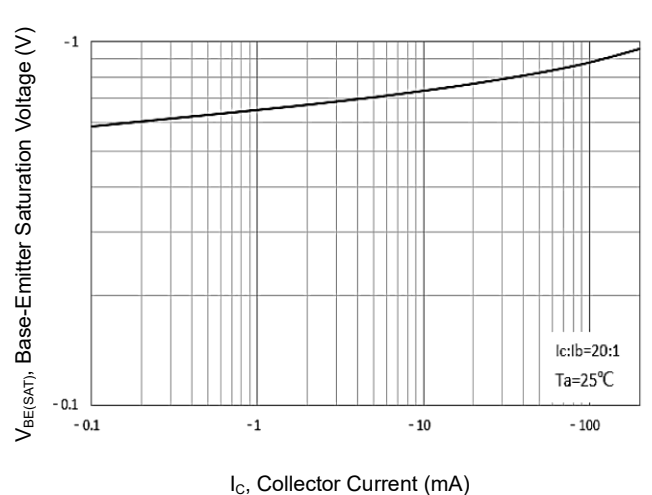
Output Characteristics



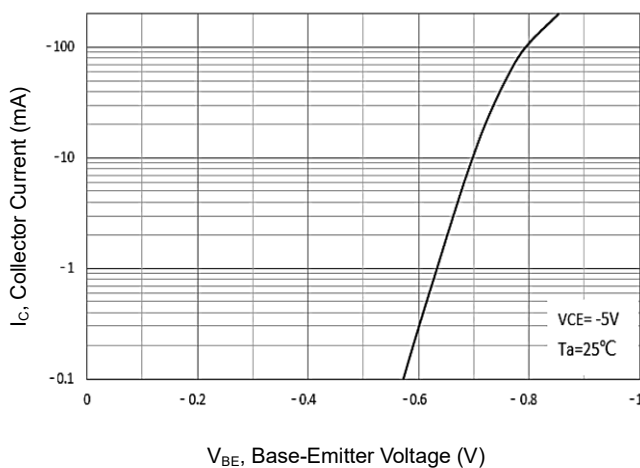
Collector-Emitter Saturation Voltage



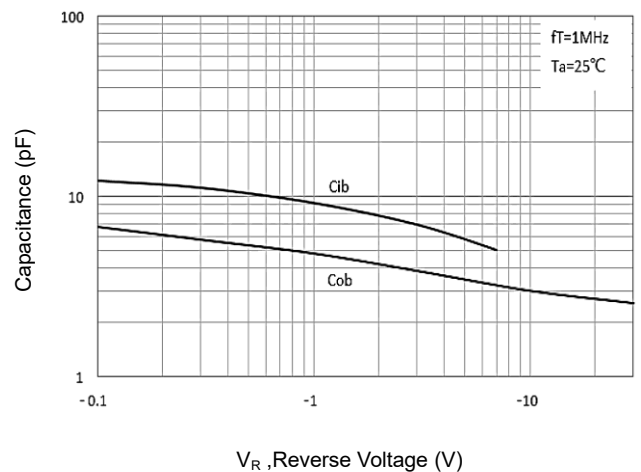
Base-Emitter Saturation Voltage



Collector Current vs. Base-Emitter Voltage



Capacitance Characteristics



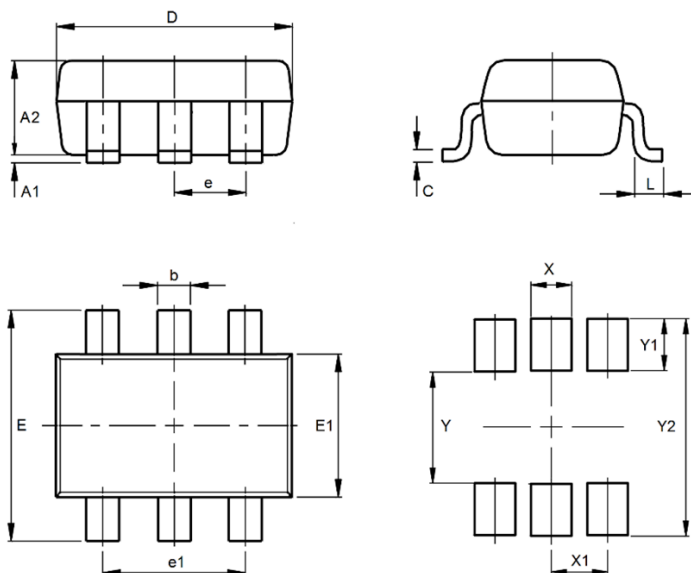
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DIMENSIONS

Item	Min (mm)	Max (mm)
A1	0.00	0.10
A2	0.85	1.05
b	0.10	0.30
c	0.10	0.25
D	1.80	2.20
e	0.60	0.70
e1	1.30	
E	2.15	2.45
E1	1.15	1.35
L	0.25	0.46
X	0.40	
X1	0.65	
Y	1.14	
Y1	0.80	
Y2	2.74	



*Specifications subject to change without notice.